L	Hits	Search Text	DB	Time stamp
Number 6	431	((silicon adj nitride) and SiN or	USPAT	2003/12/02
	431	"Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with	JULAI	15:52
8	307	(selective or selectively or selectivity) (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with	USPAT	2003/12/02 10:01
,		(selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant)		
9	282	((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting	USPAT	2003/12/02
i		or implantation or dope or doped or doping or dopant)) and (etch or etching) and @ay<=2001		
10	167	<pre>(((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or</pre>	USPAT	2003/12/02 15:36
	21	doping or dopant)) and (etch or etching) and @ay<=2001) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (al! or aluminum or Ga or gallium or boron or [8!)) [8!)]	USPAT	2003/12/02
11	21	("3886569"   "4806199"   "4807016"   "5275972"   "5286344"   "5300463"   "5424570"   "5468342"   "5562801"   "5626716"   "5695658"   "5759888"   "5814563"   "5817580"   "5841195"   "5843845"   "5843847"   "5855962"   "5965035"   "6051870"   "6239017").PN.	OSFAI	12:08
12	290	438/705.ccls.	USPAT	2003/12/02 15:36
13	650	438/706.ccls.	USPAT	2003/12/02 15:36
14	118	348/714.ccls.	USPAT	2003/12/02 15:36
15	729	438/723.ccls.	USPAT	2003/12/02 15:36
16	393	438/724.ccls.	USPAT	2003/12/02 15:37
17	38	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)	US-PGPUB; EPO; JPO; DERWENT	2003/12/02
_	1	(selective or selectively or selectivity) 4514251.pn.	USPAT	2003/12/01
   <b>-</b> 	1044	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)	USPAT	2003/12/01 15:26
-  - 	835	(((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)	USPAT	2003/12/01 14:47

				,
_	779	((((silicon adj nitride) and SiN or	USPAT	2003/12/01
	ļ	"Si.sub.3 N.sub.4") same (aluminum or		14:47
		gallium or Ga or Al) same (implant or		}
	i '	implanting or implantation or dope or		
1	}	doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj		
1		oxide) or (silicon adj dioxide) or SiO or		Í
		SiO?sub.2)		
1_	546	(((((silicon adj nitride) and SiN or	USPAT	2003/12/01
j ,	] 340	"Si.sub.3 N.sub.4") same (aluminum or	, 001111	13:46
		gallium or Ga or Al) same (implant or		1 - 3 - 1 0
1	}		}	!
1		implanting or implantation or dope or		
ì	Ì	doped or doping or dopant)) and @ay<=2001		1
		and (etch or etching)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or SiO or	ſ	ĺ
]	}	SiO?sub.2)) and (selective or selectively	J	<u> </u>
		or selectivity)		<u>.</u>
1 -	208	(((((silicon adj nitride) and SiN or	USPAT	2003/12/01
]		"Si.sub.3 N.sub.4") same (aluminum or		14:39
	}	gallium or Ga or Al) same (implant or		
1		implanting or implantation or dope or	i	!
1	(	doped or doping or dopant)) and @ay<=2001		Í
		and (etch or etching)) and ((silicon adj		[
	[	oxide) or (silicon adj dioxide) or SiO or	ſ	1
	ļ	SiO?sub.2)) and ((selective or	]	)
		selectively or selectivity) with (nitride		1
}		or SiN or "Si.sub.3 N.sub.4"))		}
	1.45	((silicon adj nitride) and SiN or	USPAT	2003/12/01
-	147		VSERI	14:47
1		"Si.sub.3 N.sub.4") with (aluminum or	1	17.7/
	(	gallium or Ga or Al) with (implant or	(	ſ
]	j	implanting or implantation or dope or	ļ	ļ
		doped or doping or dopant)	*****	2002/20/01
-	103	(((silicon adj nitride) and SiN or	USPAT	2003/12/01
1		"Si.sub.3 N.sub.4") with (aluminum or	1	14:47
1	}	gallium or Ga or Al) with (implant or	1	1
	].	implanting or implantation or dope or		1
1	<b>(</b>	doped or doping or dopant)) and @ay<=2001	1	1
		and (etch or etching)		1
Í !	94	((((silicon adj nitride) and SiN or	USPAT	2003/12/01
)	}	"Si.sub.3 N.sub.4") with (aluminum or	J	14:47
1		gallium or Ga or Al) with (implant or		-
}	)	implanting or implantation or dope or	}	1
]	]	doped or doping or dopant)   and @ay<=2001	•	1
1	}	and (etch or etching)) and ((silicon adj	1	1
		oxide) or (silicon adj dioxide) or SiO or	ļ	1
1	<b>(</b>			1
	1201	SiO?sub.2)	Henam	2002/12/01
1 ~	1391	((silicon adj nitride) and SiN or	USPAT	2003/12/01
1	]	"Si.sub.3 N.sub.4") same (oxide or	Į	15:27
		dioxide or SiO or "SiO?sub.2") same	ļ	
1	1	(selective or selectively or selectivity)	}	0000/50/55
~	1090	(((silicon adj nitride) and SiN or	USPAT	2003/12/01
1	ĺ	"Si.sub.3 N.sub.4") same (oxide or	t	15:26
		dioxide or SiO or "SiO?sub.2") same		1
1	[	(selective or selectively or	{	
1		selectivity)) and (implant or implanting	}	1
1		or implantation or dope or doped or	!	ì
	ļ	doping or dopant)	}	1
_	405	((silicon adj nitride) and SiN or	USPAT	2003/12/01
1	1	"Si.sub.3 N.sub.4") same (oxide or	1	16:40
		dioxide or SiO or "SiO?sub.2") same		1 "
	[	(selective or selectively or selectivity)	1	1
		same (implant or implanting or	1	j
		1	1	
Į	1	implantation or dope or doped or doping	1	1
	200	or dopant)	LISDAM	2003/12/01
-	398	(((silicon adj nitride) and SiN or	USPAT	) · · · · ·
	Ì	"Si.sub.3 N.sub.4") same (oxide or		15:27
		dioxide or SiO or "SiO?sub.2") same	i	
		(selective or selectively or selectivity)	1	
[	[	same (implant or implanting or		1
	] .	implantation or dope or doped or doping	1	1
L		or dopant)) and @ay<=2001	<u> </u>	<u> </u>
		0/0/00 0 50 00 70		

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<del></del>	86 ((((silicon adj nitride) and SiN or	USPAT	2003/12/01
	"Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity same (implant or implanting or implantation or dope or doped or doping or dopant) and @ay<=2001) not ((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=200 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO o. SiO?sub.2))		15:27
	((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not ((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=200 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO o SiO?sub.2))) and (etch or etching)		2003/12/01 15:27
	((((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not ((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=200 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))		2003/12/01
	(((((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not ((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=200 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO o SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))) and @py<=2001	ı	2003/12/01

. . .

	<del></del>		220000	2002/12/00
	134	(((((((silicon adj nitride) and SiN or	USPAT	2003/12/02
]		"Si.sub.3 N.sub.4") same (oxide or	]	09:59
		dioxide or SiO or "SiO?sub.2") same		•
Ì		(selective or selectively or selectivity)	ļ	1
		same (implant or implanting or	}	<b>}</b>
		implantation or dope or doped or doping	,	,
		or dopant)) and @ay<=2001) not		
[		(((((silicon adj nitride) and SiN or		1
1		"Si.sub.3 N.sub.4") with (aluminum or	}	1
1		gallium or Ga or Al) with (implant or	ļ	J :
		implanting or implantation or dope or	•	
		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj		Ì
		oxide) or (silicon adj dioxide) or SiO or		1
		SiO?sub.2))) and (etch or etching)) and	j	j .
		((implant or implanting or implantation		i
		or dope or doped or doping or dopant)	Ì	Î
		with (aluminum or al or boron or B! or		1
1	,	Ga! or gallium))) and @py<=2001) and		1
		(((silicon adj nitride) and SiN or	l	1
	Ì	"Si.sub.3 N.sub.4") with (oxide or		
1		dioxide or SiO or "SiO?sub.2"))	1	1
L	L	dioxide of 310 of 310;5db.2 ))	L	<del> </del>